

Vishay Siliconix

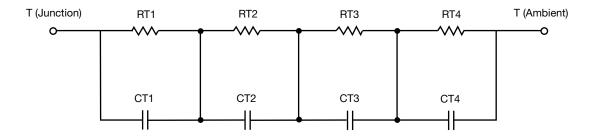
R-C Thermal Model Parameters

DESCRIPTION

The parametric values in the R-C thermal model have been derived using curve-fitting techniques. R-C values for the electrical circuit in the Foster/tank and Cauer/filter configurations are included. When implemented in PSpice, these values have matching characteristic curves to the single-pulse transient thermal impedance curves for the MOSFET.

These RC values can be used in the PSpice simulation to evaluate the thermal behavior of the MOSFET junction temperature under a defined power profile. These techniques are described in application note AN609, "Thermal Simulation of Power MOSFETs on the PSpice Platform".

R-C THERMAL MODEL FOR TANK CONFIGURATION



THERMAL RESISTANCE (°C/W)					
Junction to	Ambient	Case	Foot		
RT1	n/a	289.3437m	n/a		
RT2	n/a	317.6157m	n/a		
RT3	n/a	441.1785m	n/a		
RT4	n/a	751.8620m	n/a		
	THERMAL CAPAC	ITANCE (Joules/°C)			
Junction to	Ambient	Case	Foot		
CT1	n/a	84.3304m	n/a		
CT2	n/a	5.2638m	n/a		
CT3	n/a	3.2712m	n/a		
CT4	n/a	291.8507m	n/a		

Note

• n/a indicates not applicable

This document is intended as a SPICE modeling guideline and does not constitute a commercial product datasheet. Designers should refer to the appropriate datasheet of the same number for guaranteed specification limits.

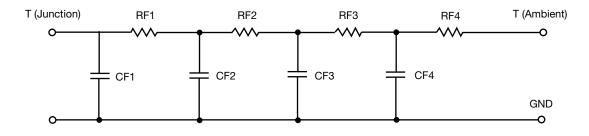
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R-C THERMAL MODEL FOR FILTER CONFIGURATION



VALUES FOR FILTER CONFIGURATION THERMAL RESISTANCE (°C/W)					
RF1	n/a	820.9807m	n/a		
RF2	n/a	511.0642m	n/a		
RF3	n/a	476.5641m	n/a		
RF4	n/a	20.6333m	n/a		
	THERMAL CAPAC	ITANCE (Joules/°C)			
Junction to	Ambient	Case	Foot		
CF1	n/a	1.9844m	n/a		
CF2	n/a	86.5352m	n/a		
CF3	n/a	417.6130m	n/a		
CF4	n/a	2.0833	n/a		

Note

• n/a indicates not applicable



SiHU4N80E_RC

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